Session Program

Nov 18 – 20, 2019

35th RD50 Workshop (CERN)

Sensor Characterization Techniques (TCT, CV); Extreme Fluences

CERN, 30/7-018 - Kjell Johnsen Auditorium
30/7-018

Wed, November 20

9:00 AM

Sensor Characterization Techniques (TCT, CV); Extreme Fluences: Sensor Characterization Techniques (TCT, CV); Extreme Fluences

Session | **Location:** CERN, 30/7-018 - Kjell Johnsen Auditorium, 30/7-018 | **Conveners:** Marcos Fernandez Garcia, Gregor Kramberger

9:00 – 9:20 AM

Effective trapping probability of electrons in neutron irradiated Si detectors using Transient Current Technique simulations

Speaker
Mr Chakresh Jain

9:20 – 9:40 AM **TPA-TCT -- Two Photon Absorption - Transient Current Technique**

Speaker
Moritz Oliver Wiehe

9:40 – 10:00 AM **Plasma Effects in TCT-TPA**

Speaker
Francisco Rogelio Palomo Pinto

10:00 – 10:20 AM **Measurements with Si detectors irradiated to extreme fluences**

Speaker
Igor Mandic

10:20 – 10:40 AM

Effects of trapping on the collected signals from subsequent laser pulses in irradiated silicon sensors

Speaker
Leena Diehl

10:40 – 11:10 AM **Coffee Break**

11:10 – 11:30 AM

Determination of the electric field in highly-irradiated silicon sensors using edge-TCT measurements

Speaker
Gregor Kramberger

11:30 – 11:50 AM

Characterisation of 3D pixel sensors irradiated at extreme fluences

Speaker
Maria Manna

11:50 AM – 12:10 PM **Discussion Session: TCT, Extreme Fluences and Modelling**

Speaker
Gregor Kramberger

2:00 PM